Joo Hyon Noh

List of Publications by Year in descending order

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471509 526287 28 912 17 27 citations h-index g-index papers 28 28 28 1406 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Ion Migration Studies in Exfoliated 2D Molybdenum Oxide via Ionic Liquid Gating for Neuromorphic Device Applications. ACS Applied Materials & Samp; Interfaces, 2018, 10, 22623-22631.	8.0	12
2	Role of Electrical Double Layer Structure in Ionic Liquid Gated Devices. ACS Applied Materials & Samp; Interfaces, 2017, 9, 40949-40958.	8.0	24
3	Room-Temperature Activation of InGaZnO Thin-Film Transistors via He ⁺ Irradiation. ACS Applied Materials & Samp; Interfaces, 2017, 9, 35125-35132.	8.0	12
4	Amorphous Semiconductors: Ionic Liquid Activation of Amorphous Metal-Oxide Semiconductors for Flexible Transparent Electronic Devices (Adv. Funct. Mater. 17/2016). Advanced Functional Materials, 2016, 26, 2774-2774.	14.9	4
5	Focused helium-ion beam irradiation effects on electrical transport properties of few-layer WSe2: enabling nanoscale direct write homo-junctions. Scientific Reports, 2016, 6, 27276.	3.3	99
6	Ionic Liquid Activation of Amorphous Metalâ€Oxide Semiconductors for Flexible Transparent Electronic Devices. Advanced Functional Materials, 2016, 26, 2820-2825.	14.9	46
7	Programmable Electrowetting with Channels and Droplets. Micromachines, 2015, 6, 172-185.	2.9	21
8	In-situ TEM observation of structural changes in nano-crystalline CoCrCuFeNi multicomponent high-entropy alloy (HEA) under fast electron irradiation by high voltage electron microscopy (HVEM). Intermetallics, 2015, 59, 32-42.	3.9	161
9	Pulse Thermal Processing for Low Thermal Budget Integration of IGZO Thin Film Transistors. IEEE Journal of the Electron Devices Society, 2015, 3, 297-301.	2.1	9
10	Inert Gas Enhanced Laser-Assisted Purification of Platinum Electron-Beam-Induced Deposits. ACS Applied Materials & Deposits. ACS Applied Materials & Deposits. ACS	8.0	17
11	Ionic Liquid versus SiO ₂ Gated a-IGZO Thin Film Transistors: A Direct Comparison. ECS Journal of Solid State Science and Technology, 2015, 4, Q105-Q109.	1.8	23
12	Purification of Nanoscale Electron-Beam-Induced Platinum Deposits via a Pulsed Laser-Induced Oxidation Reaction. ACS Applied Materials & Samp; Interfaces, 2014, 6, 21256-21263.	8.0	45
13	Electron-Beam-Assisted Oxygen Purification at Low Temperatures for Electron-Beam-Induced Pt Deposits: Towards Pure and High-Fidelity Nanostructures. ACS Applied Materials & Deposits: 1018-1024.	8.0	73
14	MeV electron-irradiation-induced structural change in the bcc phase of Zr–Hf–Nb alloy with an approximately equiatomic ratio. Intermetallics, 2013, 38, 70-79.	3.9	57
15	Electron-irradiation-induced structural change in Zr–Hf–Nb alloy. Intermetallics, 2012, 26, 122-130.	3.9	63
16	Toward active-matrix lab-on-a-chip: programmable electrofluidic control enabled by arrayed oxide thin film transistors. Lab on A Chip, 2012, 12, 353-360.	6.0	35
17	Quantitative Calculation of Oxygen Incorporation in Sputtered IGZO Films and the Impact on Transistor Properties. Journal of the Electrochemical Society, 2011, 158, H289.	2.9	19
18	Indium Oxide Thin-Film Transistors Fabricated by RF Sputtering at Room Temperature. IEEE Electron Device Letters, 2010, 31, 567-569.	3.9	75

#	Article	IF	Citations
19	Nanofabrication of insulated scanning probes for electromechanical imaging in liquid solutions. Nanotechnology, 2010, 21, 365302.	2.6	20
20	Inducement of Azimuthal Molecular Orientation of Pentacene by Imprinted Periodic Groove Patterns for Organic Thinâ€Film Transistors. Advanced Materials, 2008, 20, 1146-1153.	21.0	29
21	Formation of stable direct current microhollow cathode discharge by venturi gas flow system for remote plasma source in atmosphere. Applied Physics Letters, 2008, 92, 061503.	3.3	3
22	Polymeric tandem organic light-emitting diodes using a self-organized interfacial layer. Applied Physics Letters, 2008, 92, .	3.3	13
23	Increase in indium diffusion by tetrafluoromethane plasma treatment and its effects on the device performance of polymer light-emitting diodes. Journal of Applied Physics, 2008, 103, 114502.	2.5	22
24	Low-Voltage-Driven Bottom-Gate Amorphous Indium–Gallium–Zinc-Oxide Thin-Film Transistors with High Dielectric Constant Oxide/Polymer Double-Layer Dielectric. Japanese Journal of Applied Physics, 2007, 46, 4096-4098.	1.5	16
25	Characterization of CF4Plasma-Treated Indium–Tin-Oxide Surfaces Used in Organic Light-Emitting Diodes by X-ray Photoemission Spectroscopy. Japanese Journal of Applied Physics, 2007, 46, 6814-6816.	1.5	4
26	High-performance and low-voltage pentacene thin film transistors fabricated on the flexible substrate. Semiconductor Science and Technology, 2007, 22, 691-694.	2.0	6
27	Low leakage current gate dielectrics prepared by ion beam assisted deposition for organic thin film transistors. Journal of Applied Physics, 2007, 102, 126101.	2.5	4
28	Self-sensing neutralizer by means of self-ejected charged particles from ac microhollow cathode discharge. Applied Physics Letters, 2006, 89, 121503.	3.3	0